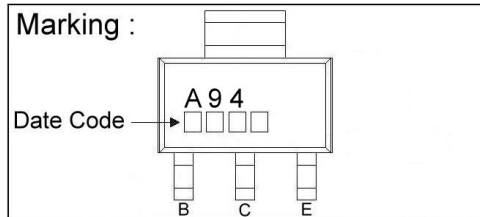
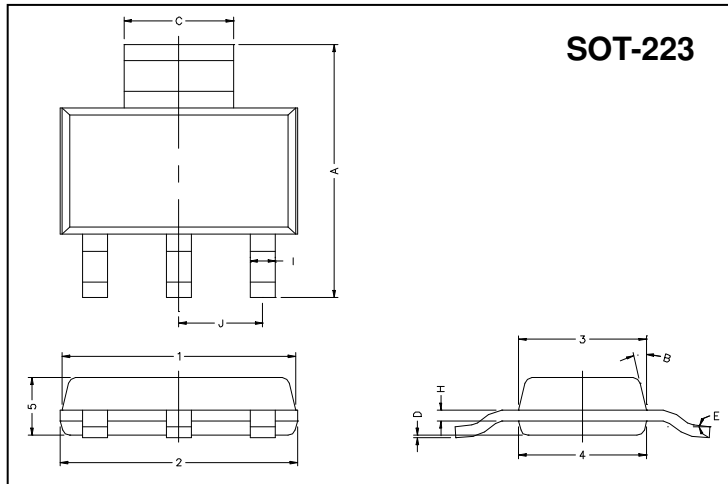


**GLA94****PNP EPITAXIAL PLANAR TRANSISTOR****Description**

The GLA94 is designed for application requires high voltage.

**Features**

- High voltage:  $V_{CEO}=400V$  (min) at  $I_C=1mA$
- High current gain:  $I_C=300mA$  at  $25^{\circ}C$
- Complementary with GLA44

**Package Dimensions**

| REF. | Millimeter |      | REF. | Millimeter |      |
|------|------------|------|------|------------|------|
|      | Min.       | Max. |      | Min.       | Max. |
| A    | 6.70       | 7.30 | B    | 13° TYP.   |      |
| C    | 2.90       | 3.10 | J    | 2.30 REF.  |      |
| D    | 0.02       | 0.10 | 1    | 6.30       | 6.70 |
| E    | 0°         | 10°  | 2    | 6.30       | 6.70 |
| I    | 0.60       | 0.80 | 3    | 3.30       | 3.70 |
| H    | 0.25       | 0.35 | 4    | 3.30       | 3.70 |
|      |            |      | 5    | 1.40       | 1.80 |

**Absolute Maximum Ratings at  $T_a = 25^{\circ}C$** 

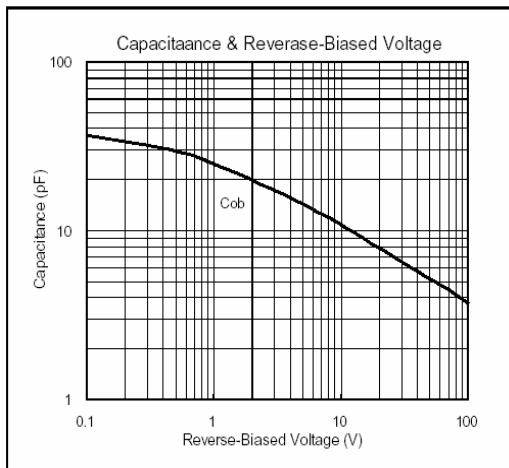
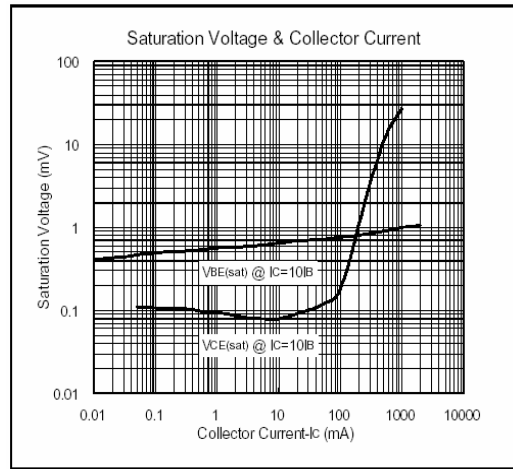
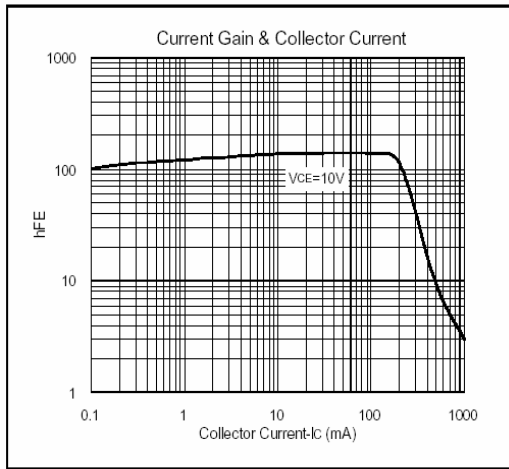
| Parameter                    | Symbol    | Ratings    | Unit        |
|------------------------------|-----------|------------|-------------|
| Junction Temperature         | $T_j$     | +150       | $^{\circ}C$ |
| Storage Temperature Range    | $T_{STG}$ | -55 ~ +150 | $^{\circ}C$ |
| Collector to Base Voltage    | $V_{CBO}$ | -400       | V           |
| Collector to Emitter Voltage | $V_{CEO}$ | -400       | V           |
| Emitter to Base Voltage      | $V_{EBO}$ | -6         | V           |
| Collect Current(DC)          | $I_C$     | -500       | mA          |
| Total Power Dissipation      | $P_D$     | 2          | W           |

**Electrical Characteristics ( $T_a = 25^{\circ}C$ )**

| Symbol           | Min. | Typ. | Max. | Unit | Test Conditions           |
|------------------|------|------|------|------|---------------------------|
| $BVC_{BO}$       | -400 | -    | -    | V    | $I_C=-100\mu A, I_E=0$    |
| $BV_{CEO}$       | -400 | -    | -    | V    | $I_C=-1mA, I_B=0$         |
| $BVE_{BO}$       | -6   | -    | -    | V    | $I_E=-100\mu A, I_C=0$    |
| $IC_{BO}$        | -    | -    | -100 | nA   | $V_{CB}=-400V, I_E=0$     |
| $IC_{ES}$        | -    | -    | -500 | nA   | $V_{CE}=-400V, V_{BE}=0$  |
| $IE_{BO}$        | -    | -    | -100 | nA   | $V_{EB}=-6V, I_C=0$       |
| * $V_{CE(sat)1}$ | -    | -    | -350 | mV   | $I_C=-1mA, I_B=-0.1mA$    |
| * $V_{CE(sat)2}$ | -    | -    | -500 | mV   | $I_C=-10mA, I_B=-1mA$     |
| * $V_{CE(sat)3}$ | -    | -    | -750 | mV   | $I_C=-50mA, I_B=-5mA$     |
| * $V_{BE(sat)}$  | -    | -    | -750 | mV   | $I_C=-10mA, I_B=-1mA$     |
| * $h_{FE1}$      | 40   | -    | -    |      | $V_{CE}=-10V, I_C=-1mA$   |
| * $h_{FE2}$      | 50   | -    | 300  |      | $V_{CE}=-10V, I_C=-10mA$  |
| * $h_{FE3}$      | 45   | -    | -    |      | $V_{CE}=-10V, I_C=-50mA$  |
| * $h_{FE4}$      | 40   | -    | -    |      | $V_{CE}=-10V, I_C=-100mA$ |

\* Pulse Test: Pulse Width  $\leq 380\mu s$ , Duty Cycle  $\leq 2\%$

## Characteristics Curve

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